

3.3 V Dual Channel High Speed - 10 MBit/s Logic Gate Optocouplers

HCPL062N

Description

The HCPL062N optocouplers consist of an AlGaAs LED, optically coupled to a very high speed integrated photo–detector logic gate consisting of bipolar transistors on a CMOS process for reduced power consumption. The output features an open collector, thereby permitting wired OR outputs. The devices are housed in a compact small–outline package. The coupled parameters are guaranteed over the temperature range of -40° C to $+85^{\circ}$ C. An internal noise shield and provides superior common mode rejection.

Features

- Compact SO8 Package
- Very High Speed 10 MBit/s
- Superior CMR 25 kV/µs Minimum (1,000 Volts Common Mode)
- Logic Gate Output
- Wired OR-open Collector
- Fixed Threshold Detector Design Minimizes Thermal Impact on Switching Times
- U.L. Recognized (File # E90700)

Applications

- Ground Loop Elimination
- Field Buses
- Line Receiver, Data Transmission
- Data Multiplexing
- Switching Power Supplies
- Pulse Transformer Replacement
- Computer-peripheral Interface
- Instrumentation Input/Output Isolation

TRUTH TABLE (POSITIVE LOGIC)

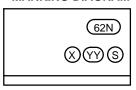
Input	Output
Н	L
L	Н

A 0.1 µF bypass capacitor must be connected between pins 8 and 5.



SOIC8 CASE 751DZ

MARKING DIAGRAM



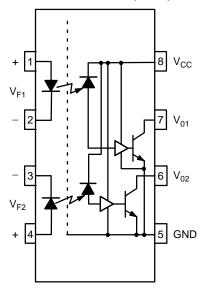
62N = Device number

K = One digit year code, e.g., '3'

YY = Two digit work week ranging from '01' to '53'

S = Assembly package code

CIRCUIT DRAWING (Note 1)



NOTE:

 The V_{CC} supply to each optoisolator must be bypassed by a 0.1 μF capacitor or larger. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected no further than 3 mm from the V_{CC} and GND pins of each device.

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (No derating required up to 85°C)

Symbol	Parameter	Value	Unit	
T _{STG}	Storage Temperature	-40 to +125	°C	
T _{OPR}	Operating Temperature	-40 to +85	°C	
ITTER				
I _F	DC/Average Forward Input Current (Each Channel)	50	mA	
V _R	Reverse Input Voltage (Each Channel)	5.0	V	
P _I	Power Dissipation	45	mW	
TECTOR				
V _{CC} minute max)	Supply Voltage	7.0	V	
I _O	Output Current (Each Channel)	15	mA	
Vo	Output Voltage (Each Channel)	7.0	V	
Po	Collector Output Power Dissipation	85	mW	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
I _{FL}	Input Current, Low Level	0	250	μΑ
I _{FH}	Input Current, High Level	6.3 (Note 2)	15	mA
V _{CC}	Supply Voltage, Output	2.7	3.3	V
T _A	Operating Temperature	-40	+85	°C
N	Fan Out (TTL load)	-	5	TTL Loads
R _L	Output Pull-up	330	4K	Ω

^{2. 6.3} mA is a guard banded value which allows for at least 20% CTR degradation. Initial input current threshold value is 5.0 mA or less

ELECTRICAL CHARACTERISTICS ($T_A = -40^{\circ}C$ to $+85^{\circ}C$, unless otherwise specified)

INDIVIDUAL COMPONENT CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ (Note 3)	Max	Unit
EMITTER	T di dinotoi	Tool Containent		(**************************************	max	U
V _F	Input Forward Voltage	I _F = 10 mA	_	_	1.8	V
		I _F = 10 mA, T _A = 25°C	-	_	1.75	1
B_VR	Input Reverse Breakdown Voltage	$I_R = 10 \mu A$	5.0	_	_	V
$\Delta V_F / \Delta T_A$	Input Diode Temperature Coefficient	I _F = 10 mA	-	-1.5	_	mV/°C
DETECTOR						
I _{CCH}	High Level Supply Current	$I_F = 0 \text{ mA}, V_{CC} = 3.3 \text{ V}$	_	7.1	10	mA
I _{CCL}	Low Level Supply Current	$I_F = 10 \text{ mA}, V_{CC} = 3.3 \text{ V}$	_	6.7	15	mA

SWITCHING CHARACTERISTICS ($T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = 3.3$ V, $I_F = 7.5$ mA, unless otherwise specified)

Symbol	AC Characteristics	Test Conditions	Min	Typ (Note 3)	Max	Unit
T _{PLH}	Propagation Delay Time to Output High Level	$R_L = 350 \ \Omega, \ C_L = 15 \ pF$ Note 4, Figure 10	-	-	90	ns
T _{PHL}	Propagation Delay Time to Output Low Level	$R_L = 350 \ \Omega, \ C_L = 15 \ pF$ Note 5, Figure 10	-	-	75	ns
T _{PHL} -T _{PLH}	Pulse Width Distortion	$R_L = 350 \ \Omega$, $C_L = 15 \ pF$ Figure 10	_	-	25	ns
t _r	Output Rise Time (10–90%)	$R_L = 350 \ \Omega, \ C_L = 15 \ pF$ Note 6, Figure 10	_	16	-	ns
t _f	Output Fall Time (90–10%)	$R_L = 350 \ \Omega, \ C_L = 15 \ pF$ Note 7, Figure 10	-	4	-	ns
CM _H	Common Mode Transient Immunity (at Output High Level)	$\begin{array}{l} R_L = 350 \; \Omega, \; T_A = 25^{\circ} C, \; I_F = 0 \; mA, \\ V_{CC} = 3.3 \; V, \; V_{O(Min.)} = 2 \; V \\ V_{CM} = 1,000 \; V \\ Notes \; 8, \; 11, \; Figure \; 11 \end{array}$	25,000	-	-	V/µs
CM _L	Common Mode Transient Immunity (at Output Low Level)	$\begin{array}{l} {\sf R_L=350~\Omega,T_A=25^{\circ}C,I_F=7.5~mA,} \\ {\sf V_{CC}=3.3~V,V_{O(Max.)}=0.8~V} \\ {\sf V_{CM} =1,000~V} \\ {\sf Notes~9,~11,Figure~11} \end{array}$	25,000	-	-	V/µs

TRANSFER CHARACTERISTICS ($T_A = -40^{\circ}\text{C}$ to +85°C, unless otherwise specified)

Symbol	AC Characteristics	Test Conditions	Min	Typ (Note 3)	Max	Unit
V _{OL}	Low Level Output Voltage	$V_{CC} = 3.3 \text{ V}, I_F = 5 \text{ mA}, I_{OL} = 13 \text{ mA}$	ı	-	0.6	V
I _{FT}	Input Threshold Current	$V_{CC} = 3.3 \text{ V}, V_{O} = 0.6 \text{ V}, I_{OL} = 13 \text{ mA}$	ı	ı	5	mA

ISOLATION CHARACTERISTICS (T_A = -40°C to +85°C, unless otherwise specified)

Symbol	AC Characteristics	Test Conditions	Min	Typ (Note 3)	Max	Unit
I _{I-O}	Input-Output Insulation Leakage Current	Relative humidity = 45%, T_A = 25°C, t = 5 s V_{I-O} = 3000 VDC, Note 10	-	-	1.0	μΑ
V _{ISO}	Withstand Insulation Test Voltage	$R_H < 50\%$, $T_A = 25$ °C $I_{I-O} \le 2 \mu A$, $t = 1 \text{ min.}$, Note 10	2500	-	-	V _{RMS}
R _{I-O}	Resistance (Input to Output)	V _{I-O} = 500 V, Note 10	ı	1012	-	Ω
C _{I–O}	Capacitance (Input to Output)	f = 1 MHz, Note 10	_	0.6	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 3. All typical values are at V_{CC} = 3.3 V, T_A = 25°C unless otherwise specified.
- 4. tpLH Propagation delay is measured from the 3.75 mA level on the HIGH to LOW transition of the input current pulse to the 1.5 V level on the LOW to HIGH transition of the output voltage pulse.
- t_{PHL} Propagation delay is measured from the 3.75 mA level on the LOW to HIGH transition of the input current pulse to the 1.5 V level on the HIGH to LOW transition of the output voltage pulse.
- 6. t_r Rise time is measured from the 90% to the 10% levels on the LOW to HIGH transition of the output pulse. 7. t_f Fall time is measured from the 10% to the 90% levels on the HIGH to LOW transition of the output pulse.
- 8. CM_H The maximum tolerable rate of rise of the common mode voltage to ensure the output will remain in the high state (i.e., V_{OLT} > 2.0 V). Measured in volts per microsecond (V/ μ s).
- CM_L The maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the low output state (i.e., V_{OUT} < 0.8 V). Measured in volts per microsecond (V/μs).
- 10. Device considered a two-terminal device: Pins 1, 2, 3 and 4 shorted together, and Pins 5, 6, 7 and 8 shorted together.
- 11. The power supply bypass capacitors must be no further than 3 mm from the leads of the optocoupler. A low inductance ground plane width of with ≤ 5 nHy of series lead inductance is required.

TYPICAL PERFORMANCE CURVES

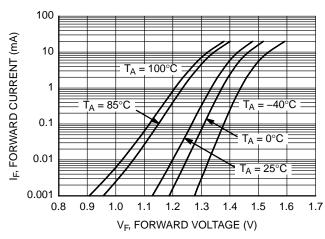


Figure 1. Forward Current vs. Forward Voltage

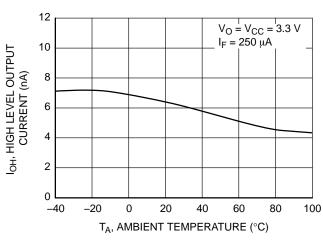


Figure 2. High Level Output Current vs.

Ambient Temperature

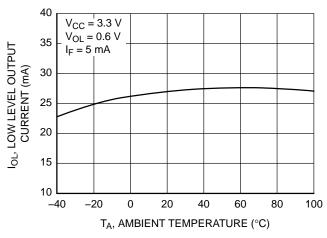


Figure 3. Low Level Output Current vs.

Ambient Temperature

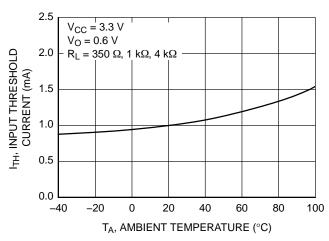


Figure 4. Input Threshold Current vs. Temperature

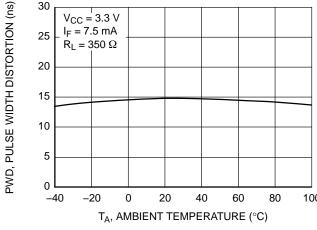


Figure 5. Pulse Width Distortion vs. Ambient Temperature

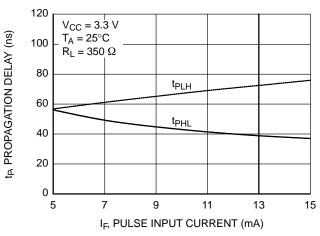


Figure 6. Propagation Delay vs. Pulse Input Current

TYPICAL PERFORMANCE CURVES (Continued)

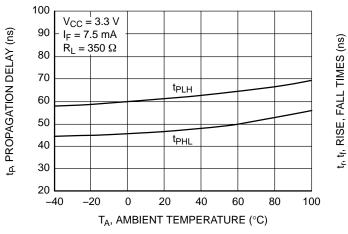


Figure 7. Propagation Delay vs. Ambient Temperature

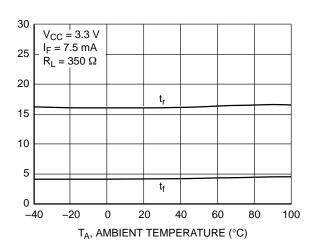


Figure 8. Rise and Fall Times vs. Ambient Temperature

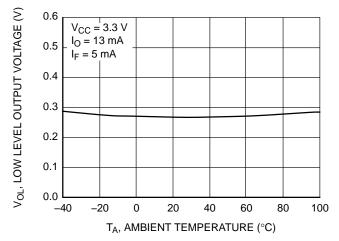


Figure 9. Low Level Output Voltage vs. Ambient Temperature

TEST CIRCUITS

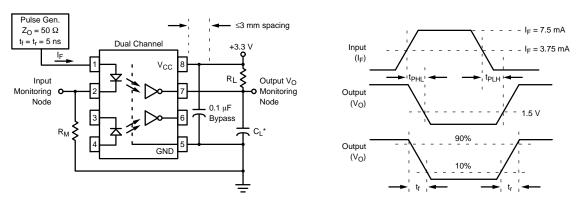


Figure 10. Test Circuit and Waveforms for $t_{\mbox{\scriptsize PLH}},\,t_{\mbox{\scriptsize PHL}},\,t_{\mbox{\scriptsize r}}$ and $t_{\mbox{\scriptsize f}}$

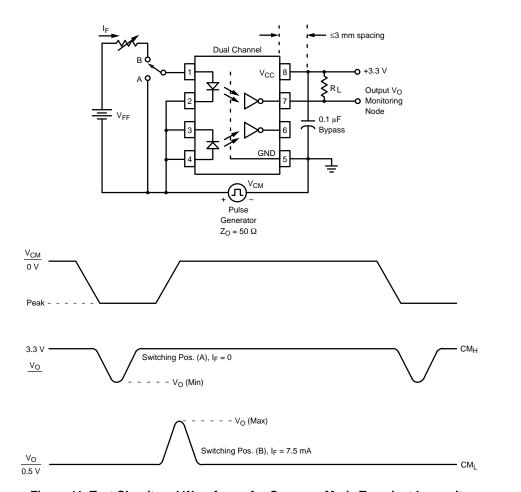


Figure 11. Test Circuit and Waveforms for Common Mode Transient Immunity

REFLOW PROFILE

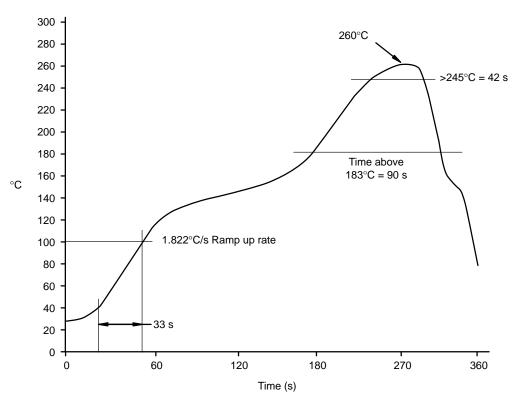


Figure 12. Reflow Profile

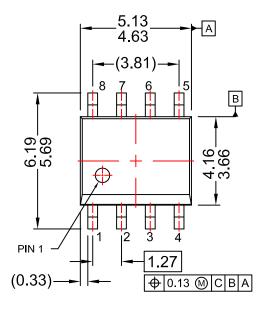
ORDERING INFORMATION

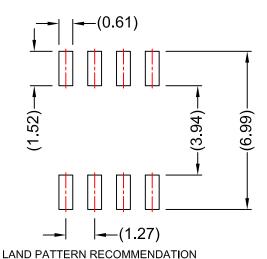
Option	Order Entry Identifier	Package Type	Shipping [†]
No Suffix	HCPL062N	SOIC8	50 Units / Tube
R2	HCPL062NR2	(Pb–Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

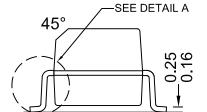
SOIC8 CASE 751DZ ISSUE O

DATE 30 SEP 2016





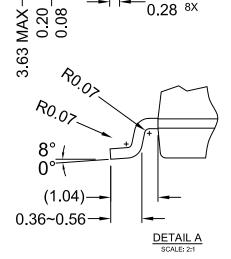
0.53 0.28 8X



END VIEW

NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
- D) LANDPATTERN STANDARD: SOIC127P600X175-8M.



DOCUMENT NUMBER:	98AON13733G	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC8		PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems. or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales